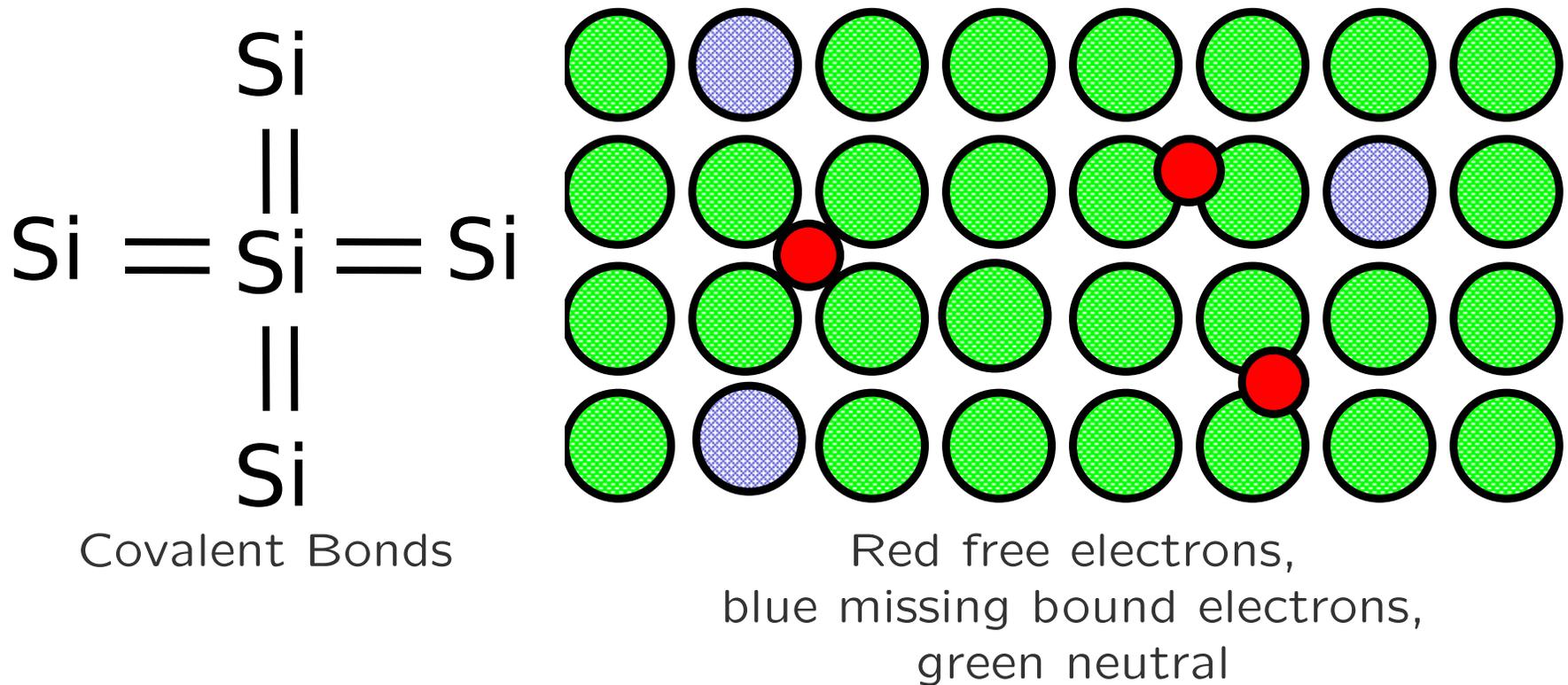


# Intrinsic Semiconductor



# N-Doped Semiconductor

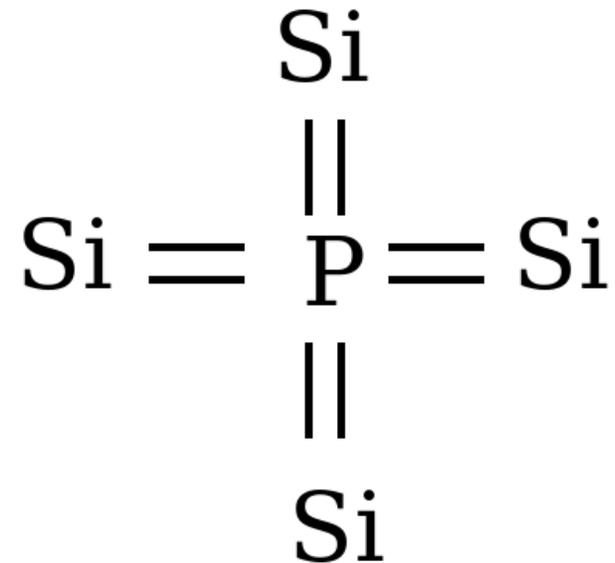
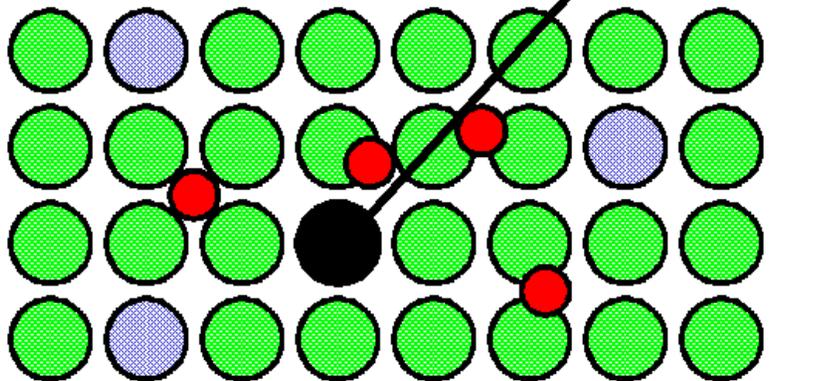
N-Doping

Phosphorus has Valence=5

One Extra Valence Electron

One Extra Proton

Still Charge Neutral



Electrons Are  
Majority Carriers

# P-Doped Semiconductor

P-Doping

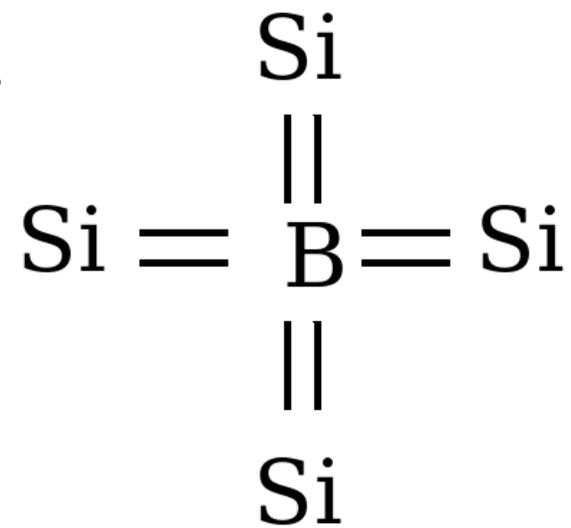
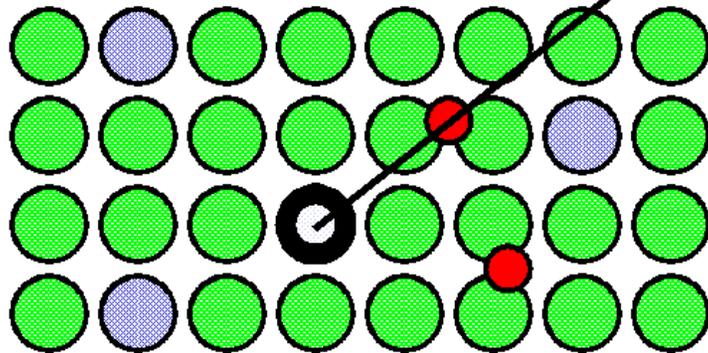
Boron has Valence=3

Short One Valence Electron

One Free Electron Replaces It

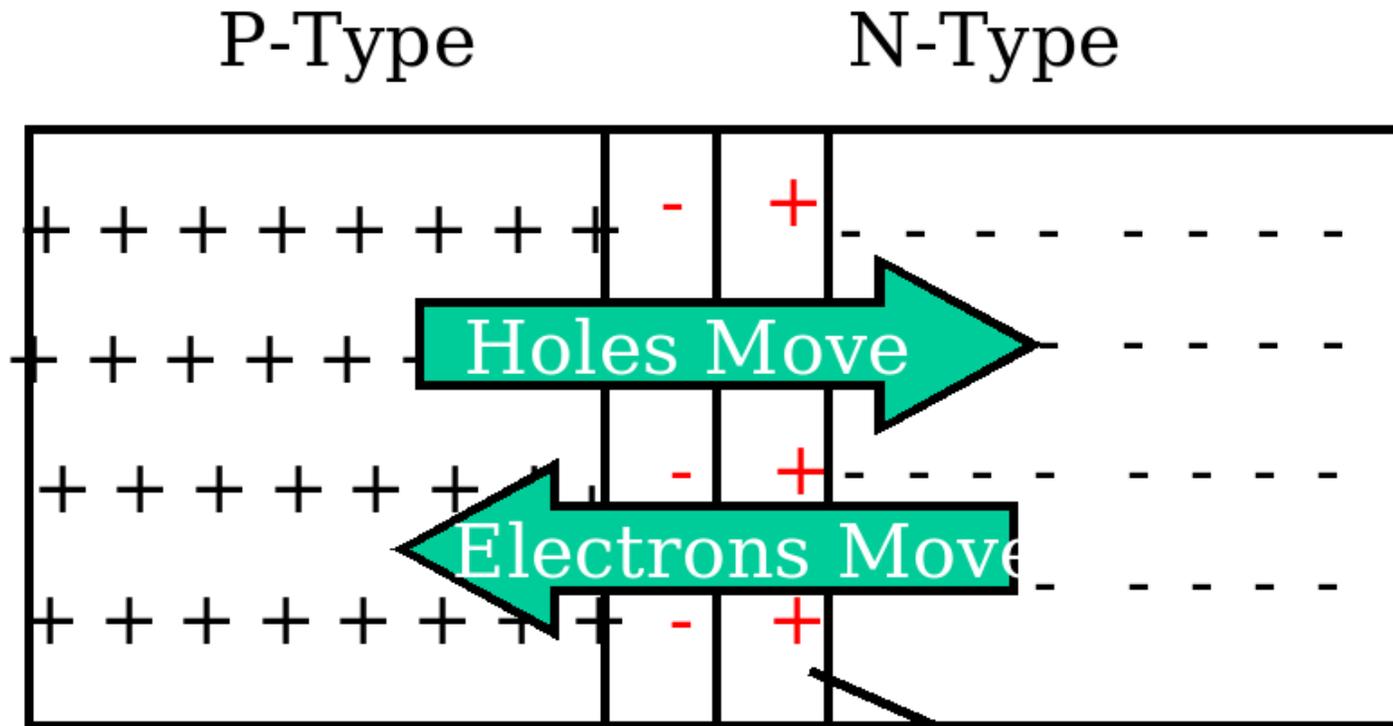
Short One Proton

Still Charge Neutral



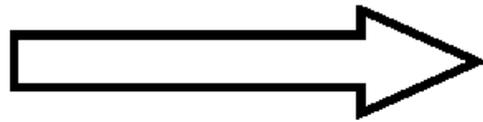
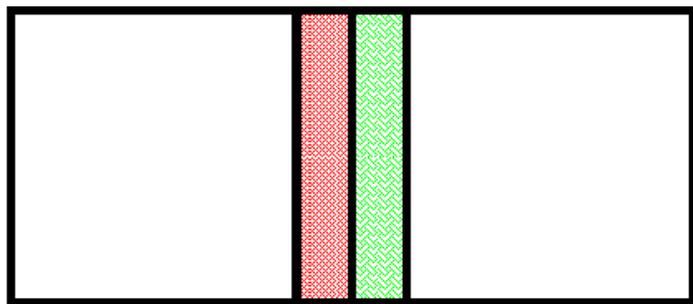
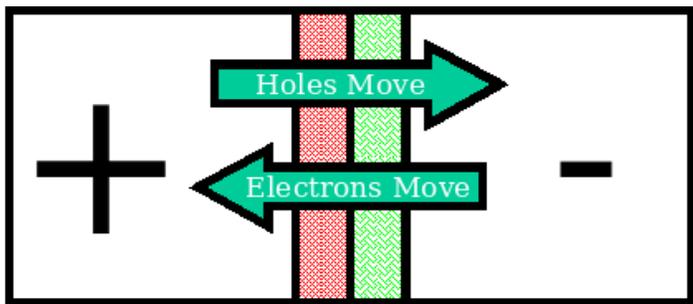
Holes Are Majority Carriers

# Junction

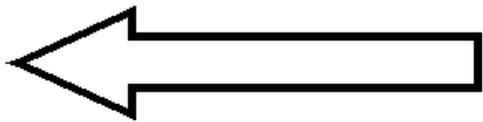


Free charges diffuse across boundary and  
Expose **Bound Charges**

# Diffusion and Drift (Zero Bias)



Diffusion Current,  $I_D$



Drift Current,  $I_S$

$$I_D = I_S$$